

Title (en)  
NOVEL SILICON CARBIDE DUMMY WAFER

Title (de)  
NEUER SILICIUMCARBID ERSATZWAFER

Title (fr)  
NOUVELLE TRANCHE VIERGE AU CARBURE DE SILICIUM

Publication  
**EP 0758310 A1 19970219 (EN)**

Application  
**EP 96908623 A 19960228**

Priority  
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Abstract (en)  
[origin: WO9626910A1] The present invention relates to an unsiliconized or siliconized wafer consisting essentially of recrystallized silicon carbide, the wafer having a diameter of at least 150 mm and a thickness of between 0.5 and 2 mm, and having a porosity or free silicon content between 15 v/o and 43 v/o.

IPC 1-7  
**C04B 35/573**; C30B 31/10; C04B 41/87; C04B 38/00

IPC 8 full level  
**C04B 35/565** (2006.01); **C04B 35/573** (2006.01); **C04B 38/00** (2006.01); **C04B 41/87** (2006.01); **C30B 25/02** (2006.01); **H01L 21/02** (2006.01)

CPC (source: EP KR)  
**C04B 35/573** (2013.01 - EP KR); **C04B 35/575** (2013.01 - EP); **C04B 35/62655** (2013.01 - EP); **C04B 35/632** (2013.01 - EP); **C04B 35/63424** (2013.01 - EP); **C04B 38/00** (2013.01 - EP); **C04B 41/009** (2013.01 - EP); **C04B 41/5059** (2013.01 - EP); **C04B 41/87** (2013.01 - EP); **C30B 25/02** (2013.01 - EP); **C30B 29/06** (2013.01 - EP); **C04B 2235/3826** (2013.01 - EP); **C04B 2235/428** (2013.01 - EP); **C04B 2235/5472** (2013.01 - EP); **C04B 2235/6027** (2013.01 - EP); **C04B 2235/608** (2013.01 - EP); **C04B 2235/61** (2013.01 - EP); **C04B 2235/616** (2013.01 - EP); **C04B 2235/661** (2013.01 - EP); **C04B 2235/77** (2013.01 - EP); **C04B 2235/95** (2013.01 - EP)

C-Set (source: EP)  
1. **C04B 38/00 + C04B 20/0076 + C04B 35/565 + C04B 38/0051 + C04B 38/0074 + C04B 41/4531 + C04B 41/5059**  
2. **C04B 38/00 + C04B 20/0076 + C04B 35/565 + C04B 38/0051 + C04B 38/0074 + C04B 41/5035**  
3. **C04B 38/00 + C04B 20/0076 + C04B 35/565 + C04B 38/0051 + C04B 38/0074 + C04B 41/5096**  
4. **C04B 41/5059 + C04B 41/4531**  
5. **C04B 41/009 + C04B 35/565**  
6. **C04B 41/009 + C04B 35/573**  
7. **C04B 41/009 + C04B 38/00**

Citation (search report)  
See references of WO 9626910A1

Designated contracting state (EPC)  
AT BE CH DE DK ES FR GB GR IE IT LI LU MC NL PT SE

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